

# INC1001AC1

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

INC1001AC1 is a silicon NPN epitaxial type transistor.  
It is designed with high collector current and small  $V_{CE(sat)}$ .

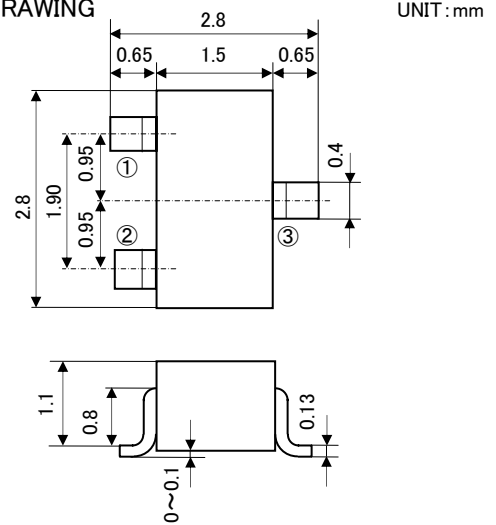
## FEATURE

- Super mini package for easy mounting
- High collector current ( $I_C=500\text{mA}$ )
- Low collector saturation voltage  
( $V_{CE(sat)} < 0.25V_{max}$ ;  $I_C=100\text{mA}$ ,  $I_B=10\text{mA}$ )

## APPLICATION

For switching, Small type motor drive

## OUTLINE DRAWING



Terminal Connector

JEITA:SC-59

①: Base

JEDEC: Similar to TO-236

②: Emitter

③: Collector

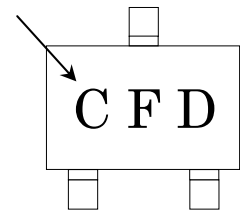
## MAXIMUM RATING ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CEO}$	Collector to Emitter voltage	80	V
$V_{CBO}$	Collector to Base voltage	80	V
$V_{EBO}$	Emitter to Base voltage	7	V
$I_C$	Collector current	0.5	A
$P_C$	Collector dissipation( $T_a=25^\circ\text{C}$ )	200	mW
		500(*)	
$T_j$	Junction temperature	+150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~+150	$^\circ\text{C}$

\*Mounted on glass epoxy board(46mm × 19mm × 1mm)

## MARKING

Type Name



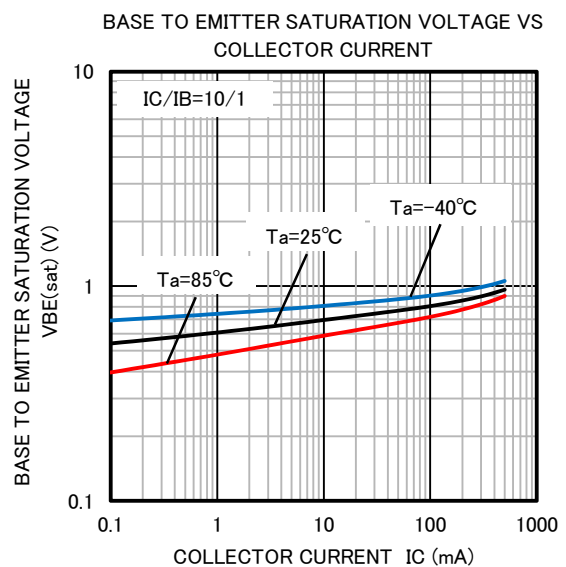
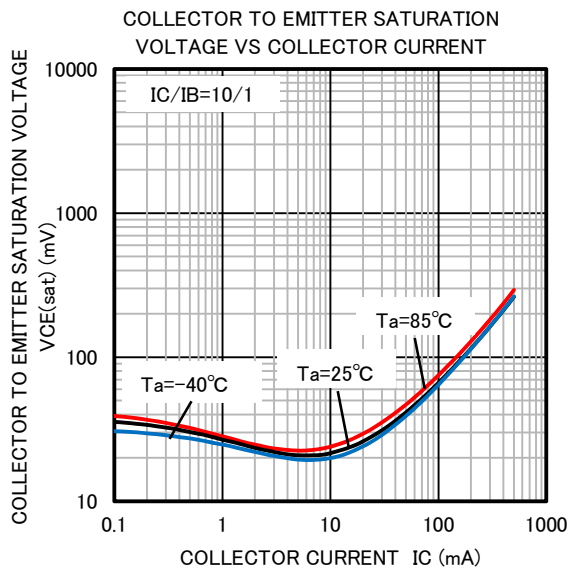
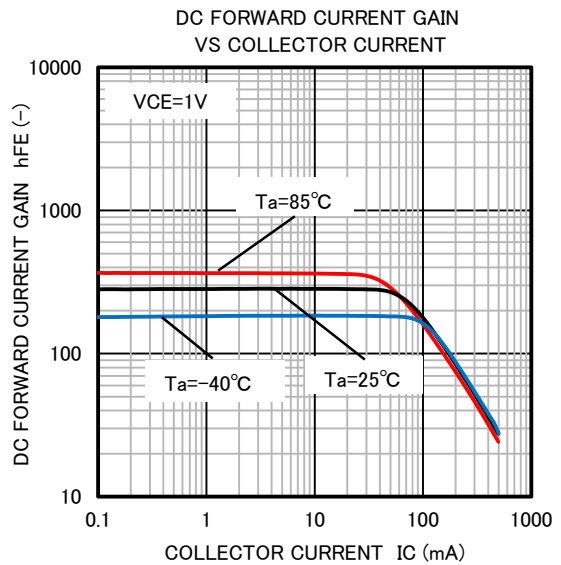
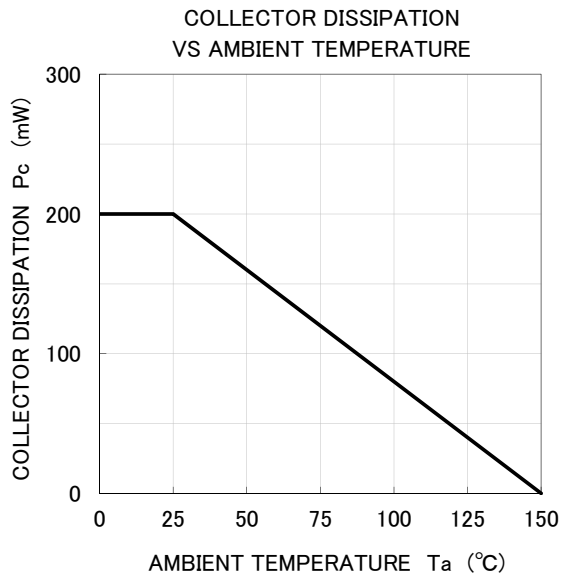
## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1\text{mA}$ , $I_B=0\text{mA}$	80	-	-	V
$V_{(BR)CBO}$	C to B break down voltage	$I_C=100\mu\text{A}$ , $I_E=0\text{mA}$	80	-	-	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=100\mu\text{A}$ , $I_C=0\text{mA}$	7	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB}=80\text{V}$ , $I_E=0\text{mA}$	-	-	0.15	$\mu\text{A}$
$I_{EBO}$	Emitter cut off current	$V_{EB}=7\text{V}$ , $I_C=0\text{mA}$	-	-	0.15	$\mu\text{A}$
hFE1	DC forward current gain1	$V_{CE}=1\text{V}$ , $I_C=10\text{mA}$	105	-	-	-
hFE2	DC forward current gain2	$V_{CE}=1\text{V}$ , $I_C=100\text{mA}$	95	-	-	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C=100\text{mA}$ , $I_B=10\text{mA}$	-	-	0.3	V
fT	Gain bandwidth product	$V_{CE}=2\text{V}$ , $I_E=-10\text{mA}$ , $f=100\text{MHz}$	100	-	-	MHz

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## TYPICAL CHARACTERISTICS





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